

# Dallas Semiconductor IME 3Q01

<b>Product</b>	<b>Tested</b>	<b>Fails</b>	<b>ppm</b>
DS2118M	12380	3	242
DS21X5Y	5182	14	2409
DS80CH11	9191	66	7181
<b>Totals for 0.6um:</b>	<b>27031</b>	<b>83</b>	<b>3071</b>
DS1232	9883	3	304
DS87C520	10936	14	1280
DS2154	12243	21	1715
<b>Totals for 0.8um:</b>	<b>31278</b>	<b>38</b>	<b>1215</b>

**Goal = 300 ppm**

Ken Wendel 4/20/01

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<b>Part No.</b>	<b>Qty</b>	<b>Fail Mechanism</b>
DS2118M	3	Could not resolve Failure
DS21352	3	Could resolve Failure
	1	In Analysis
DS21554	10	In Analysis
DS80CH11	66	In Analysis
DS1232	1	Isolated to SV Osc Circuit. FM not resolved
	2	Gate Oxide defect
DS87C520	11	Gate Oxide defect
	3	In Analysis
DS2154	21	In Analysis